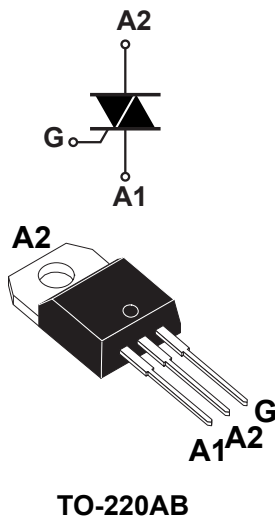


6 A 800 V Snubberless Triac in TO-220AB package



Features

- Medium current Triac
- High static and dynamic commutation
- Three quadrants
- ECOPACK2 compliant

Applications

- General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting
- Inrush current limiting circuits
- Overvoltage crowbar protection

Description

Available in through-hole package, the T635T-8T Triac can be used for the on/off or phase angle control function in general purpose AC switching where high commutation capability is required.

This device can be used without a snubber circuit when the limits defined in this datasheet are respected.

Product status link

[T635T-8T](#)

Product summary

Order code	T635T-8T
Package	TO-220AB
$I_{T(RMS)}$	6 A
V_{DRM}/V_{RRM}	800 V
V_{DSM}/V_{RSM}	900 V
I_{GT}	35 mA

1 Characteristics

Table 1. Absolute maximum ratings (limiting values)

Symbol	Parameter		Value	Unit	
$I_{T(RMS)}$	On-state RMS current (full sine wave)		$T_c = 135\text{ °C}$	6	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25 °C)	F = 50 Hz	t = 20 ms	45	A
		F = 60 Hz	t = 16.7 ms	47	
I^2t	I^2t value for fusing, (T_j initial = 25 °C)		$t_p = 10\text{ ms}$	13	A ² s
V_{DRM}/V_{RRM}	Repetitive surge peak off-state voltage		$T_j = 150\text{ °C}$	600	V
			$T_j = 125\text{ °C}$	800	
V_{DSM}/V_{RSM}	Non repetitive surge peak off-state voltage		$t_p = 10\text{ ms}$	900	V
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100\text{ ns}$		F = 100 Hz	100	A/ μ s
I_{GM}	Peak gate current	$t_p = 20\text{ }\mu$ s	$T_j = 150\text{ °C}$	4	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 150\text{ °C}$	1	W
T_{stg}	Storage junction temperature range			-40 to +150	°C
T_j	Operating junction temperature range			-40 to +150	°C
T_L	Maximum lead temperature soldering during 10 s			260	°C

Table 2. Electrical characteristics ($T_j = 25\text{ °C}$ unless otherwise specified)

Symbol	Test conditions		Value	Unit		
$I_{GT}^{(1)}$	$V_D = 12\text{ V}$, $R_L = 30\text{ }\Omega$	I - II - III	Min.	1.75	mA	
			Max.	35		
V_{GT}	$V_D = 12\text{ V}$, $R_L = 30\text{ }\Omega$	I - II - III	Max.	1.3	V	
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$, $T_j = 150\text{ °C}$	I - II - III	Min.	0.2	V	
$I_H^{(1)}$	$I_T = 500\text{ mA}$		Max.	40	mA	
I_L	$I_G = 1.2 \times I_{GT}$	I - III	Max.	60	mA	
		II		65		
dV/dt ⁽¹⁾	$V_D = 536\text{ V}$, gate open	$T_j = 125\text{ °C}$	Min.	2000	V/ μ s	
	$V_D = 402\text{ V}$, gate open	$T_j = 150\text{ °C}$		1000		
(dI/dt) _c ⁽¹⁾	Without snubber (dV/dt) _c > 20 V/ μ s		Min.	$T_j = 125\text{ °C}$	6	A/ms
				$T_j = 150\text{ °C}$	3	

1. For both polarities of A2 referenced to A1

Table 3. Static characteristics

Symbol	Test conditions			Value	Unit
$V_T^{(1)}$	$I_{TM} = 8.5 \text{ A}$, $t_p = 380 \mu\text{s}$	$T_j = 25 \text{ }^\circ\text{C}$	Max.	1.55	V
$V_{TO}^{(1)}$	Threshold voltage	$T_j = 150 \text{ }^\circ\text{C}$	Max.	0.85	
$R_d^{(1)}$	Dynamic resistance	$T_j = 150 \text{ }^\circ\text{C}$	Max.	75	m Ω
I_{DRM} , I_{RRM}	$V_D = V_R = 800 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}$	Max.	5	μA
		$T_j = 125 \text{ }^\circ\text{C}$		0.6	mA
	$V_D = V_R = 600 \text{ V}$	$T_j = 150 \text{ }^\circ\text{C}$	Max.	2.0	

1. For both polarities of A2 referenced to A1

Table 4. Thermal parameters

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	2.1	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient	60	$^\circ\text{C/W}$

1.1 Characteristics curves

Figure 1. Maximum power dissipation versus on-state RMS current (full cycle)

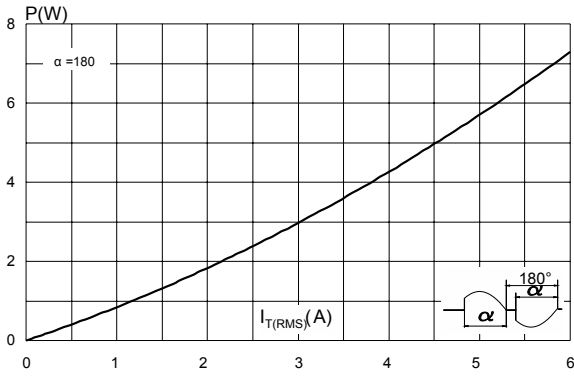


Figure 2. On-state RMS current cycle versus case temperature (full cycle)

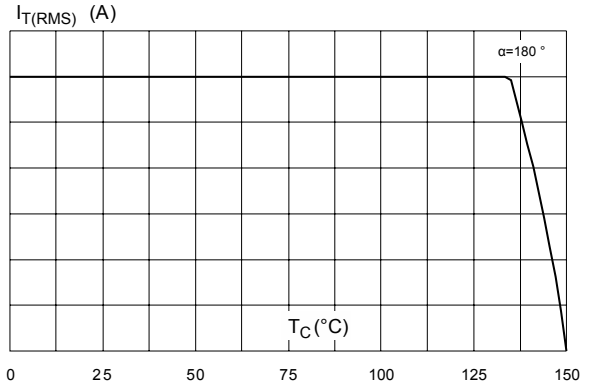


Figure 3. On-state RMS current versus ambient temperature (free air convection)

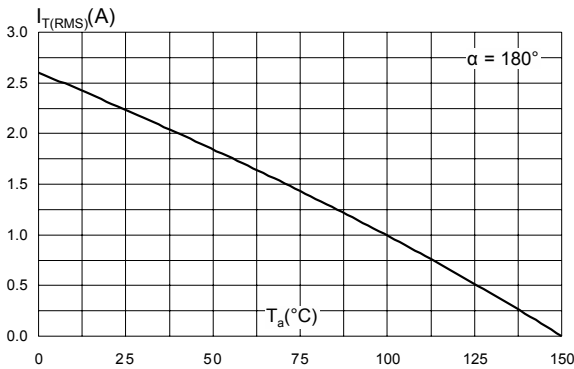


Figure 4. Relative variation of thermal impedance versus pulse duration

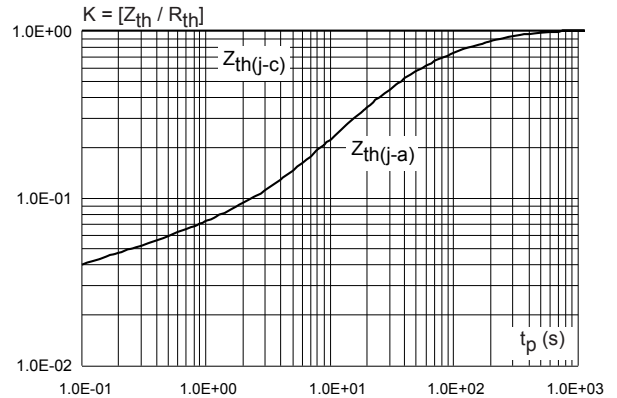


Figure 5. On-state characteristics (maximum values)

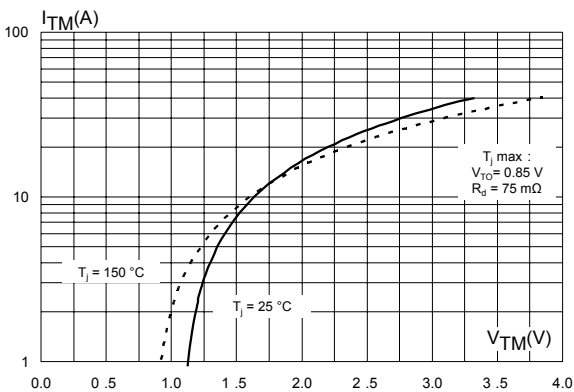


Figure 6. Surge peak on-state current versus number of cycles

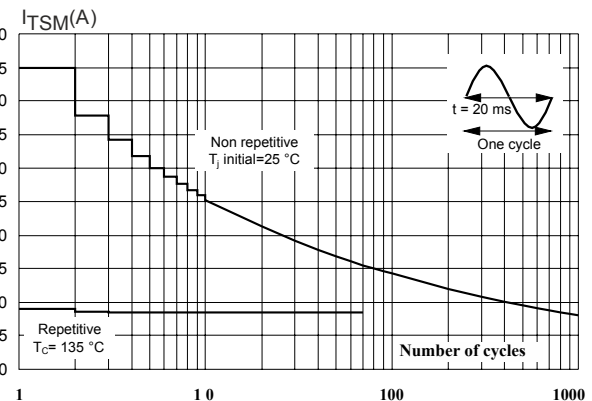


Figure 7. Non repetitive surge peak on-state current

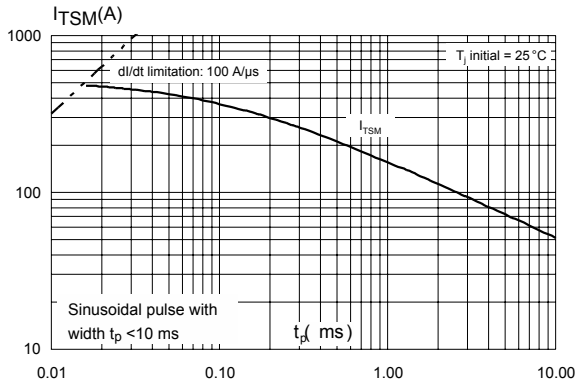


Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

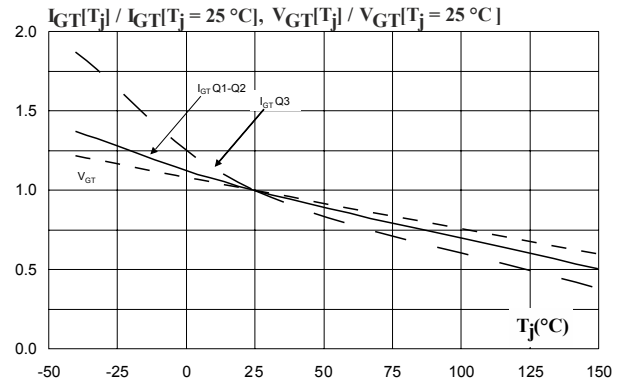


Figure 9. Relative variation of static dV/dt immunity versus junction temperature (typical values)

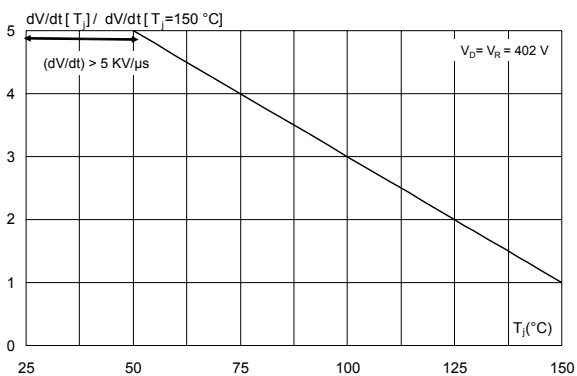


Figure 10. Relative variation of holding current and latching current versus junction temperature (typical values)

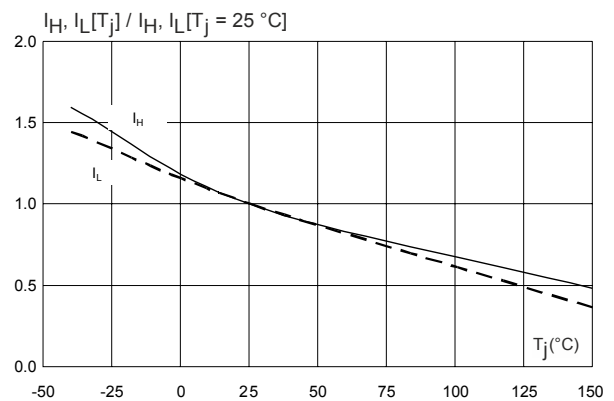


Figure 11. Relative variation of critical rate of decrease of main current (di/dt)c versus reapplied (dV/dt)c (typical values)

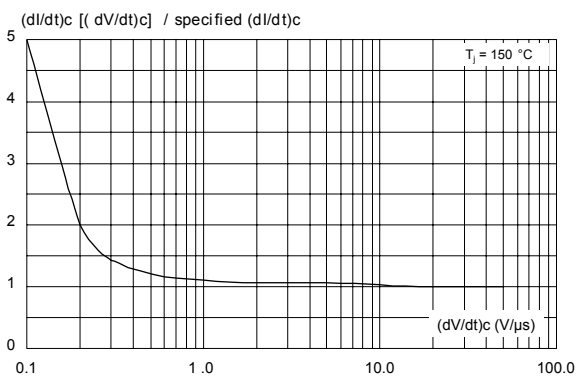


Figure 12. Relative variation of critical rate of decrease of main current (di/dt)c versus junction temperature (typical values)

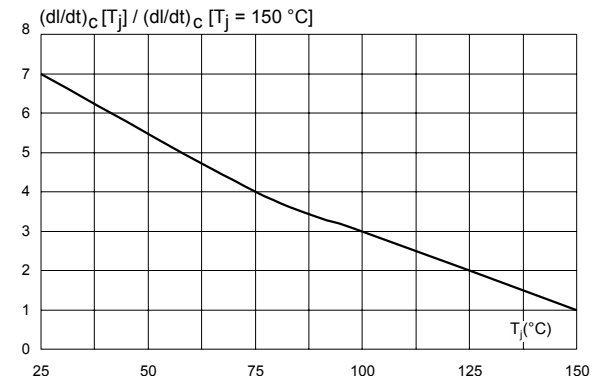


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)

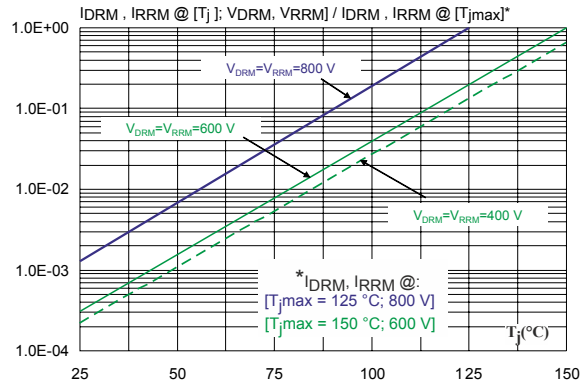


Table 5. TO-220AB package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.5984		0.6260
a1		3.75			0.1476	
a2	13.00		14.00	0.5118		0.5512
B	10.00		10.40	0.3937		0.4094
b1	0.61		0.88	0.0240		0.0346
b2	1.23		1.32	0.0484		0.0520
C	4.40		4.60	0.1732		0.1811
c1	0.49		0.70	0.0193		0.0276
c2	2.40		2.72	0.0945		0.1071
e	2.40		2.70	0.0945		0.1063
F	6.20		6.60	0.2441		0.2598
I	3.73		3.88	0.1469		0.1528
L	2.65		2.95	0.1043		0.1161
I2	1.14		1.70	0.0449		0.0669
I3	1.14		1.70	0.0449		0.0669
I4	15.80	16.40	16.80	0.6220	0.6457	0.6614
M		2.6			0.1024	

1. Inch dimensions are for reference only.

3 Ordering information

Figure 15. Ordering information scheme

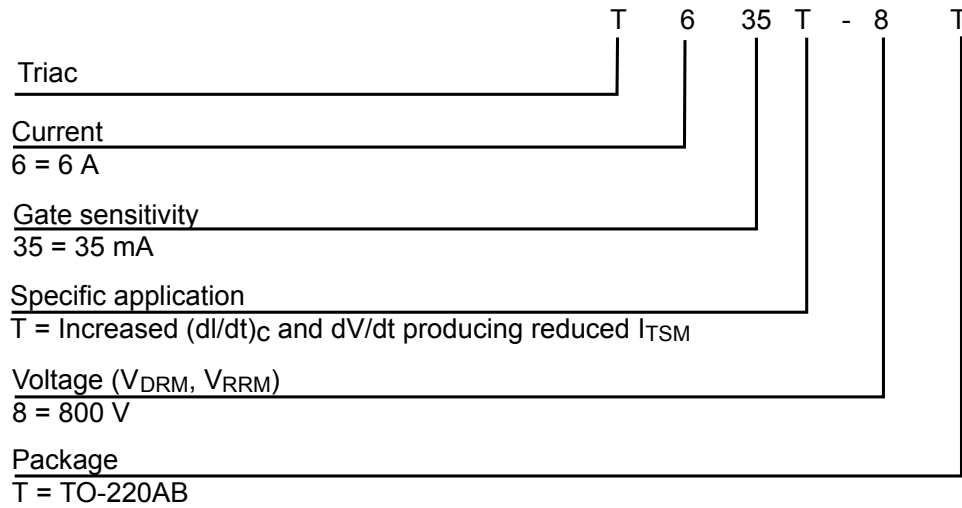


Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
T635T-8T	T635T-8T	TO-220AB	2.0 g	50	Tube

Revision history

Table 7. Document revision history

Date	Revision	Changes
05-Aug-2013	1	Initial release.
01-Jul-2014	2	Updated Table 2.
28-Jul-2014	3	Updated Table 5.
09-Sep-2019	4	Updated Figure 14 and Table 5 .

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